

PATENT

Attorney Docket No.: AMAT/8568/DSM/BCVD/JW

Express Mail No.: EV335470997US

ABSTRACT OF THE DISCLOSURE

A method for depositing a low dielectric constant film includes providing a gas mixture including a cyclic organosiloxane and N_2O as an oxidizing gas to a chamber and applying RF power to the gas mixture to deposit a low dielectric constant film. The gas mixture may also include oxygen and/or a linear hydrocarbon. In one aspect, the gas mixture includes N_2O and oxygen as oxidizing gases, and a ratio of the flow rate of the N_2O to a total flow rate of the N_2O and the oxygen is between about 0.1 and about 0.5.

231317_1